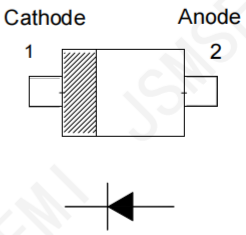
FEATURES

- Plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 µs
- Continuous reverse voltage: max. 75 V



SOD-323

APPLICATION

- Low-leakage current applications in surface mounted circuits.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V_{RRM}	repetitive peak reverse voltage		–	85	V
V_R	continuous reverse voltage		–	75	V
I_F	continuous forward current	single diode loaded; note 1; see Fig.2	–	160	mA
		double diode loaded; note 1; see Fig.2	–	140	mA
I_{FRM}	repetitive peak forward current		–	500	mA
I_{FSM}	non-repetitive peak forward current	square wave; T_j = 25 °C prior to surge; see Fig.4			
		t_p = 1 µs	——	4	A
		t_p = 1 ms		1	A
		t_p = 1 s		0.5	A
P_{tot}	total power dissipation	T_{amb} = 25 °C; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

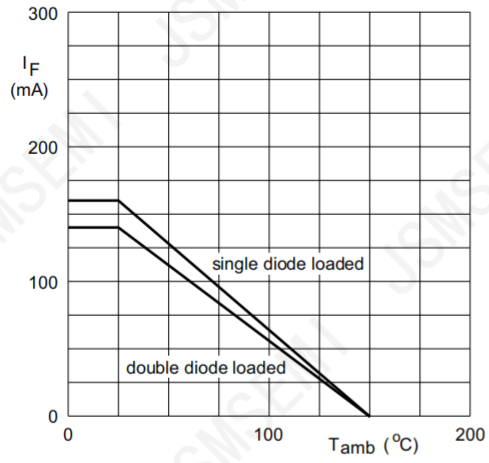
ELECTRICAL CHARACTERISTICS T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
Per diode					
V_F	forward voltage	see Fig.3			
		I_F = 1 mA	–	900	mV
		I_F = 10 mA	–	1000	mV
		I_F = 50 mA	–	1100	mV
		I_F = 150 mA	–	1250	mV
I_R	reverse current	see Fig.5			
		V_R = 75 V	0.003 3	5	nA
		V_R = 75 V; T_j = 150 °C		80	A
C_d	diode capacitance	f = 1 MHz; V_R = 0; see Fig.6	2	–	pF
t_{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA; see Fig.7	0.8	3	µs

Note

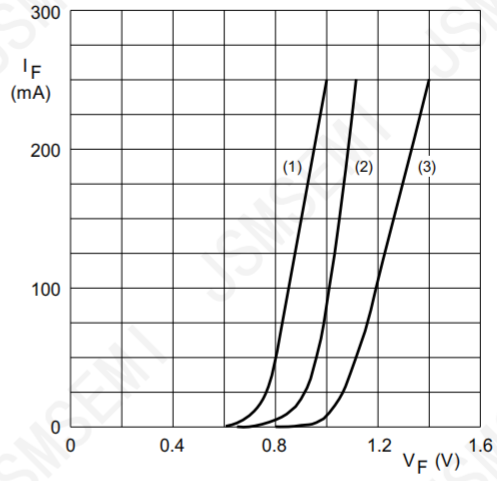
1. Device mounted on a FR4 printed-circuit board.

Typical Characteristics



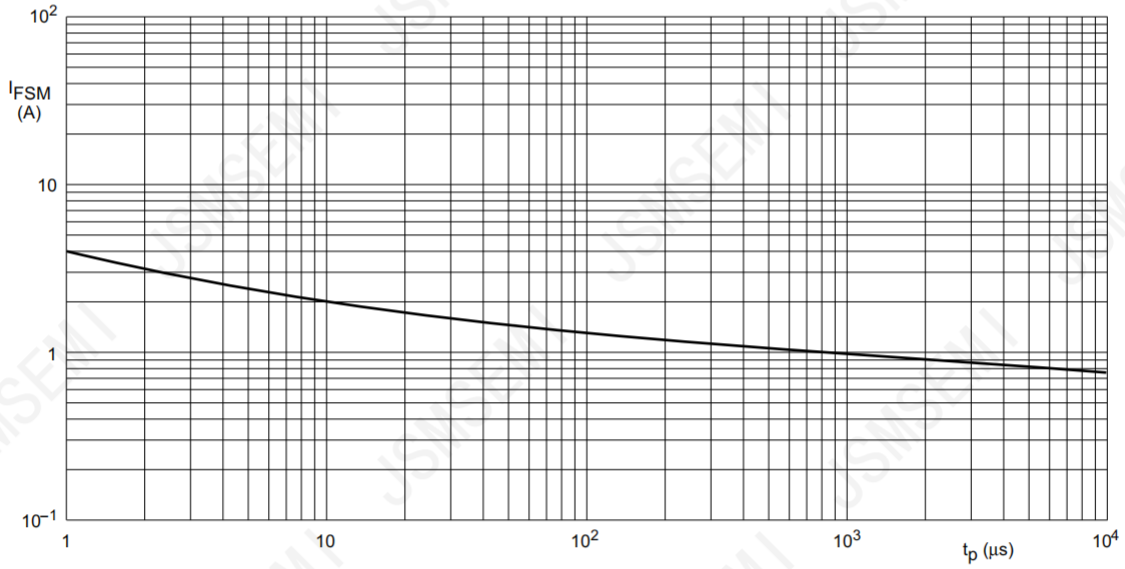
Device mounted on a FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



(1) T_j = 150 °C; typical values.
(2) T_j = 25 °C; typical values.
(3) T_j = 25 °C; maximum values.

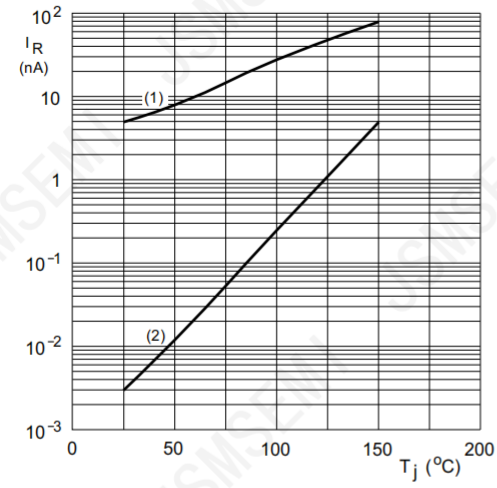
Fig.3 Forward current as a function of forward voltage; per diode.



Based on square wave currents; T_j = 25 °C prior to surge.

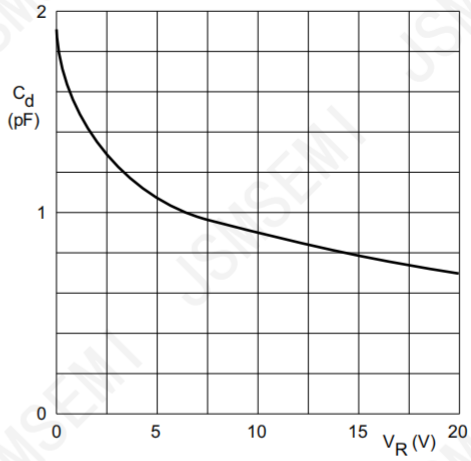
Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration per diode.

Typical Characteristics



V_R = 75 V.
(1) Maximum values.
(2) Typical values.

Fig.5 Reverse current as a function of junction temperature; per diode.

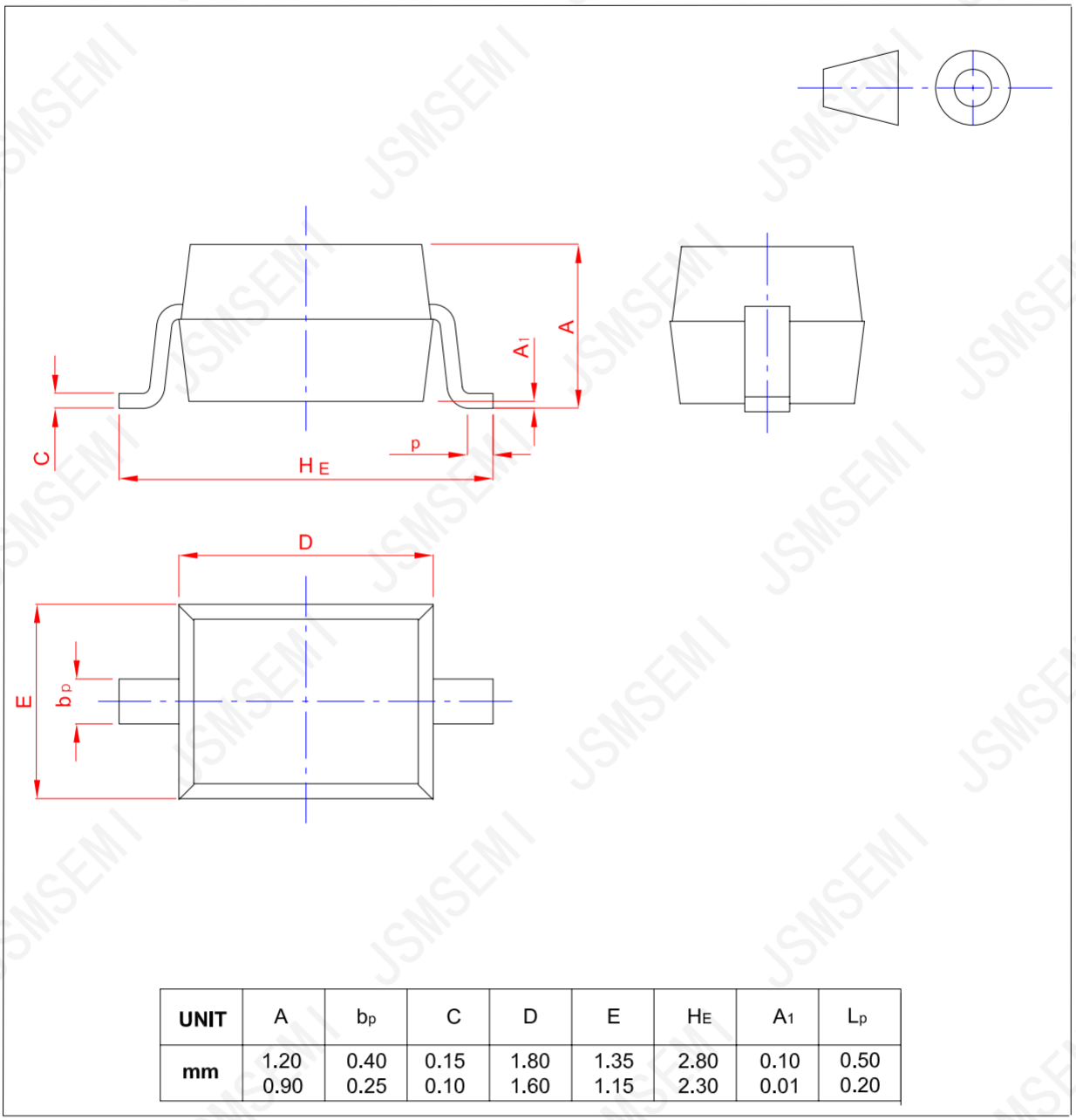


f = 1 MHz; T_j = 25 °C.

Fig.6 Diode capacitance as a function of reverse voltage; per diode; typical values.

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-323**



UNIT	A	b_p	C	D	E	H_E	A_1	L_p
mm	1.20 0.90	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30	0.10 0.01	0.50 0.20

Revision History

Rev.	Change	Date
V1.0	Initial version	2/23/2024

Important Notice

JSMSEMI Semiconductor (JSMSEMI) PRODUCTS ARE NEITHER DESIGNED NOR INTENDED FOR USE IN MILITARY AND/OR AEROSPACE, AUTOMOTIVE OR MEDICAL DEVICES OR SYSTEMS UNLESS THE SPECIFIC JSMSEMI PRODUCTS ARE SPECIFICALLY DESIGNATED BY JSMSEMI FOR SUCH USE. BUYERS ACKNOWLEDGE AND AGREE THAT ANY SUCH USE OF JSMSEMI PRODUCTS WHICH JSMSEMI HAS NOT DESIGNATED FOR USE IN MILITARY AND/OR AEROSPACE, AUTOMOTIVE OR MEDICAL DEVICES OR SYSTEMS IS SOLELY AT THE BUYER’S RISK.

JSMSEMI assumes no liability for application assistance or customer product design. Customers are responsible for their products and applications using JSMSEMI products.

Resale of JSMSEMI products or services with statements diferent from or beyond the parameters stated by JSMSEMI for that product or service voids all express and any implied warranties for the associated JSMSEMI product or s ervice. JSMSEMI is not responsible or liable for any such statements.

Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc.When designing equipment, refer to the "Delivery Specification" for the JSMSEMI product that you intend to use.

For additional information please contact Kevin@jsmsemi.com or visit www.jsmsemi.com